

N-Channel 30 V (D-S) MOSFET

PRODUCT SUMMARY

V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A) ^a	Q_g (Typ.)
30	0.046 at $V_{GS} = 4.5$ V	4	5.7 nC
	0.050 at $V_{GS} = 2.5$ V	4	
	0.057 at $V_{GS} = 1.8$ V	4	

FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFET
- 100 % R_g Tested
- Compliant to RoHS Directive 2002/95/EC

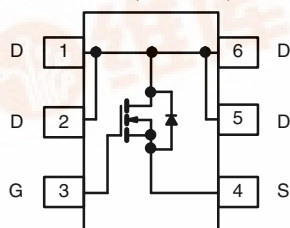


RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

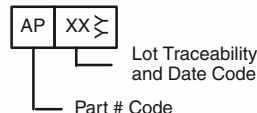
- DC/DC Converters
- Boost Converters
- Load Switches

SOT-363
SC-70 (6-LEADS)

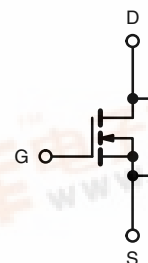


Top View

Marking Code



Ordering Information: Si1414DH-T1-GE3 (Lead (Pb)-free and Halogen-free)



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_A = 25$ °C, unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 8	
Continuous Drain Current ($T_J = 150$ °C)	I_D	$T_F = 25$ °C 4 ^a	A
		$T_F = 70$ °C 4 ^a	
		$T_A = 25$ °C 4 ^{a, b, c}	
		$T_A = 70$ °C 3.7 ^{a, b, c}	
Pulsed Drain Current	I_{DM}	20	W
Continuous Source-Drain Diode Current	I_S	$T_C = 25$ °C 2.3	
		$T_A = 25$ °C 1.3 ^{b, c}	
Maximum Power Dissipation	P_D	$T_C = 25$ °C 2.8	
		$T_C = 70$ °C 1.8	
		$T_A = 25$ °C 1.56 ^{b, c}	
		$T_A = 70$ °C 1.0 ^{b, c}	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150	°C
Soldering Recommendations (Peak Temperature) ^{d, e}		260	

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^{b, d}	R_{thJA}	60	80	°C/W
Maximum Junction-to-Foot (Drain)	R_{thJF}	34	45	

Notes:

- Package limited.
- Surface mounted on 1" x 1" FR4 board.
- $t = 5$ s.
- Maximum under steady state conditions is 125 °C/W.

Si1414DH

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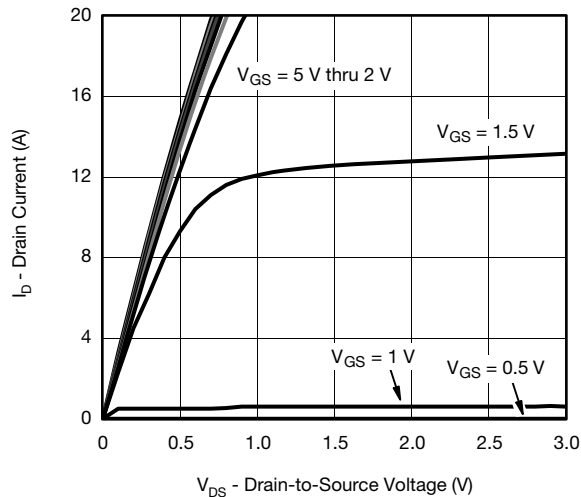
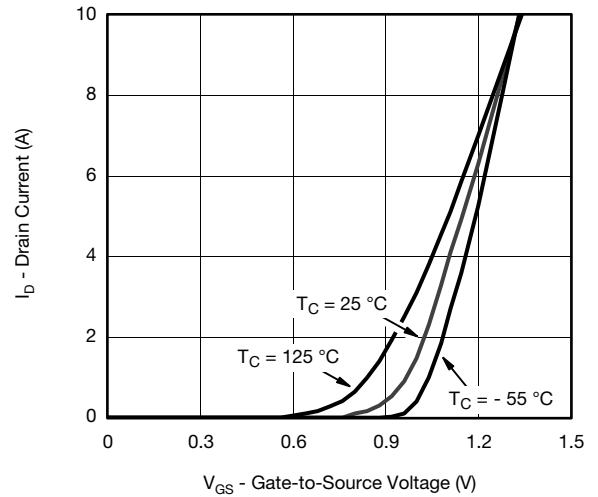
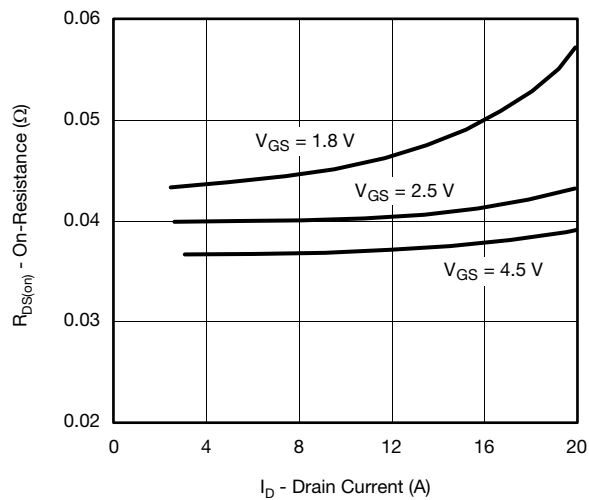
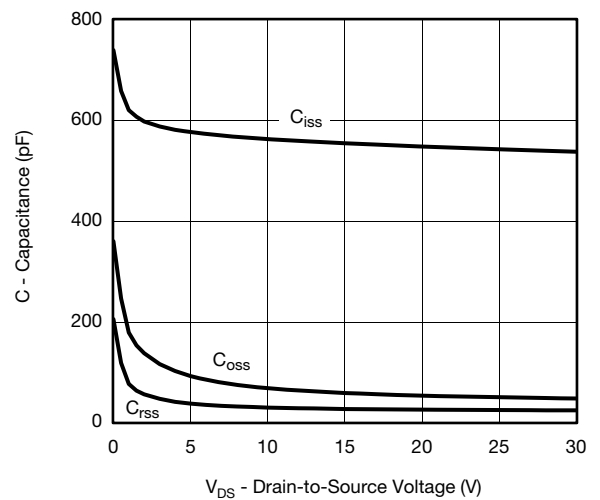
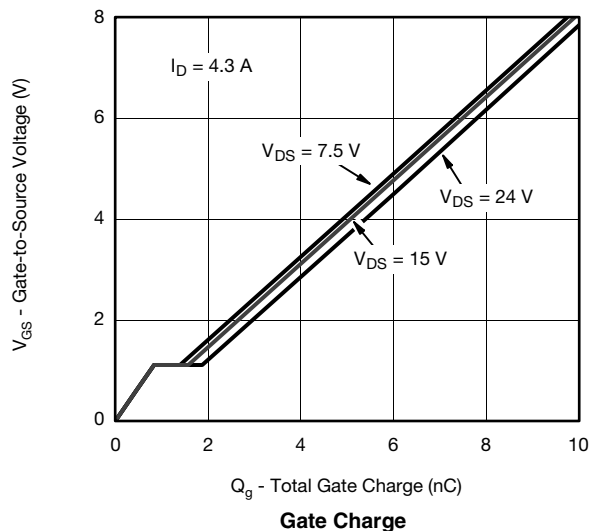
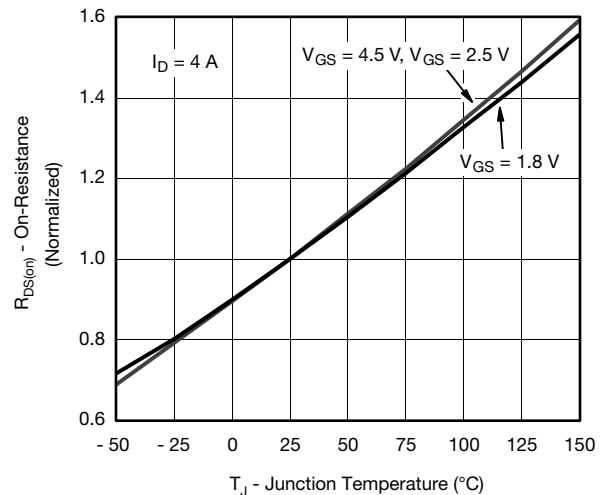
SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	30			V
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	I _D = 250 μA		31		mV/°C
V _{GS(th)} Temperature Coefficient	ΔV _{GS(th)} /T _J			- 2.7		
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	0.4		1	V
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 8 V			± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 30 V, V _{GS} = 0 V			1	μA
		V _{DS} = 30 V, V _{GS} = 0 V, T _J = 55 °C			10	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ 5 V, V _{GS} = 10 V	10			A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 4.5 V, I _D = 4 A		0.037	0.046	Ω
		V _{GS} = 2.5 V, I _D = 2 A		0.041	0.050	
		V _{GS} = 1.8 V, I _D = 1 A		0.046	0.057	
Forward Transconductance ^a	g _{fs}	V _{DS} = 15 V, I _D = 4 A		30		S
Dynamic ^b						
Input Capacitance	C _{iss}	V _{DS} = 15 V, V _{GS} = 0 V, f = 1 MHz		560		pF
Output Capacitance	C _{oss}			60		
Reverse Transfer Capacitance	C _{rss}			27		
Total Gate Charge	Q _g	V _{DS} = 15 V, V _{GS} = 10 V, I _D = 3.4 A		10	15	nC
Gate-Source Charge	Q _{gs}	V _{DS} = 15 V, V _{GS} = 4.5 V, I _D = 3.4 A		5.7	8.6	
Gate-Drain Charge	Q _{gd}			0.85		
				0.75		
Gate Resistance	R _g	f = 1 MHz	0.6	3	6	Ω
Turn-On Delay Time	t _{d(on)}	V _{DD} = 15 V, R _L = 4.3 Ω I _D ≅ 3.5 A, V _{GEN} = 4.5 V, R _g = 1 Ω		6	12	ns
Rise Time	t _r			10	20	
Turn-Off Delay Time	t _{d(off)}			20	40	
Fall Time	t _f			10	20	
Turn-On Delay Time	t _{d(on)}	V _{DD} = 15 V, R _L = 4.3 Ω I _D ≅ 3.5 A, V _{GEN} = 8 V, R _g = 1 Ω		5	10	
Rise Time	t _r			10	20	
Turn-Off Delay Time	t _{d(off)}			17	30	
Fall Time	t _f			10	20	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			1.5	A
Pulse Diode Forward Current	I _{SM}				20	
Body Diode Voltage	V _{SD}	I _S = 3.5 A, V _{GS} = 0 V		0.8	1.2	V
Body Diode Reverse Recovery Time	t _{rr}	I _F = 3.5 A, dI/dt = 100 A/μs, T _J = 25 °C		15	30	ns
Body Diode Reverse Recovery Charge	Q _{rr}			6	12	nC
Reverse Recovery Fall Time	t _a			8		ns
Reverse Recovery Rise Time	t _b			7		

Notes:

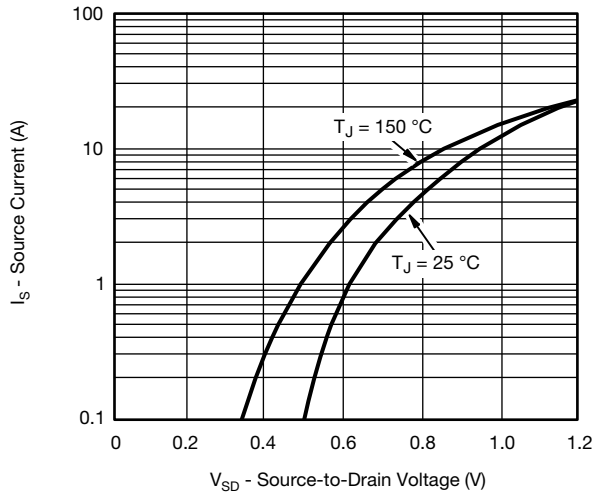
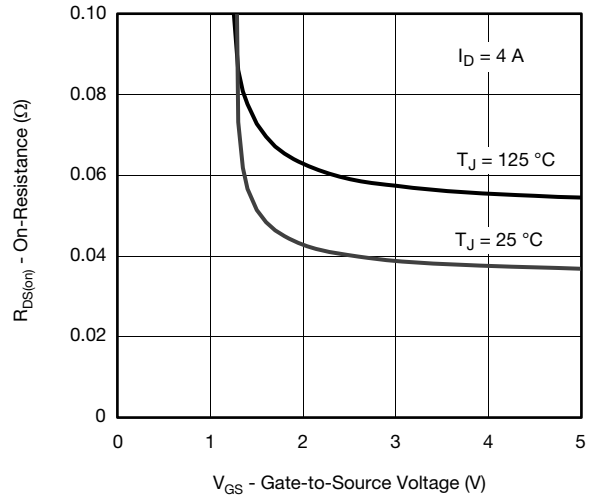
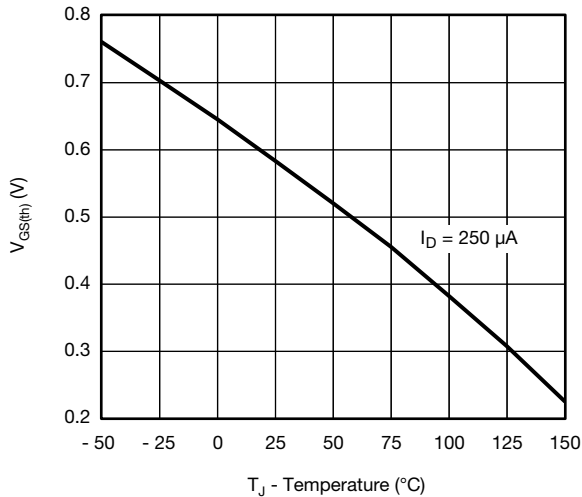
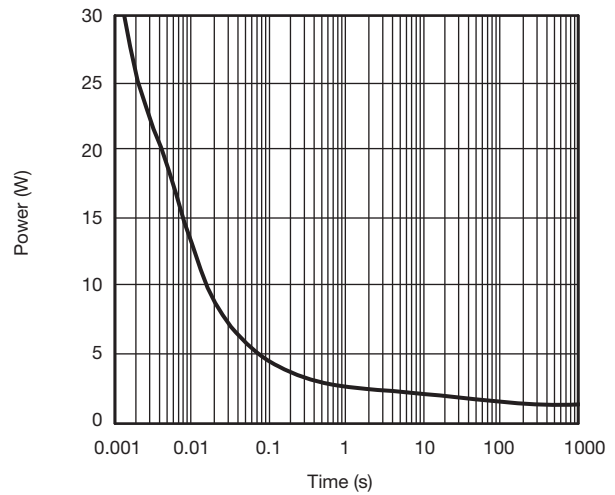
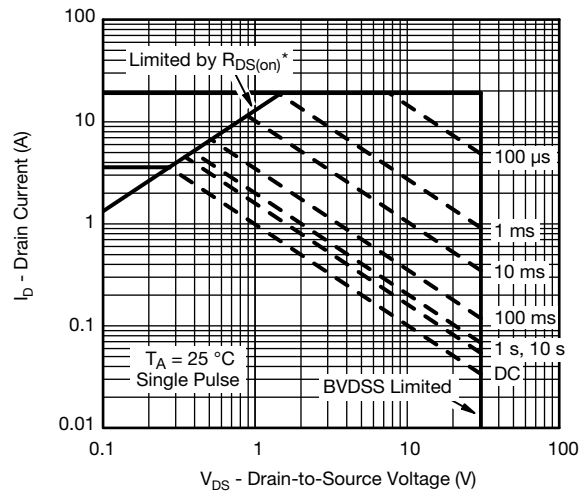
a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %

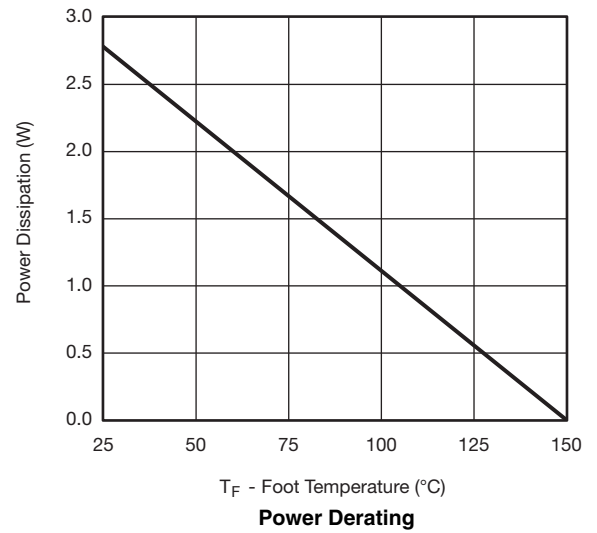
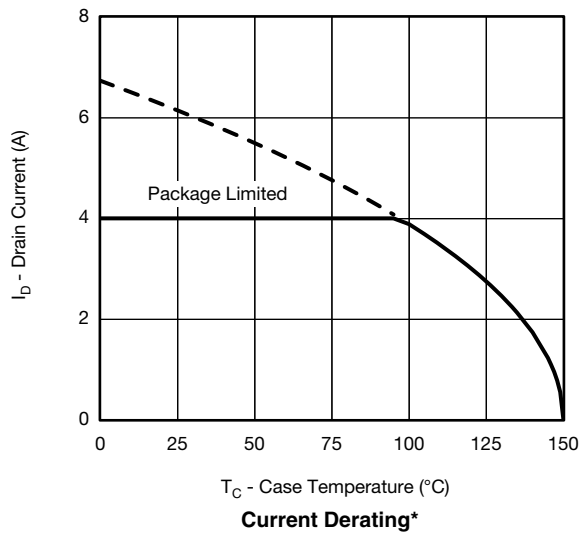
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Output Characteristics

Transfer Characteristics

On-Resistance vs. Drain Current and Gate Voltage

Capacitance

Gate Charge

On-Resistance vs. Junction Temperature

Si1414DH

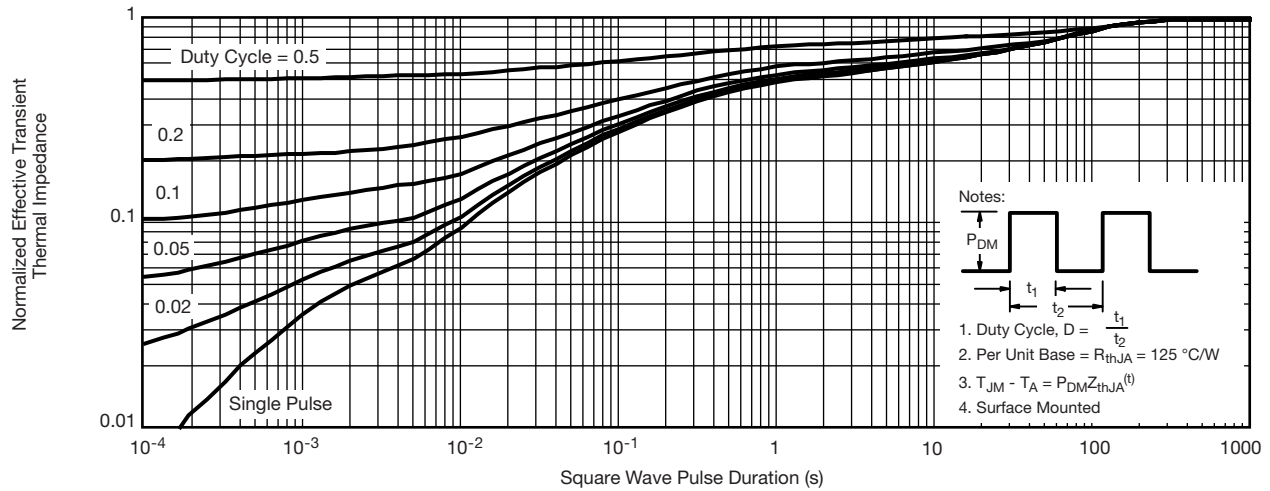
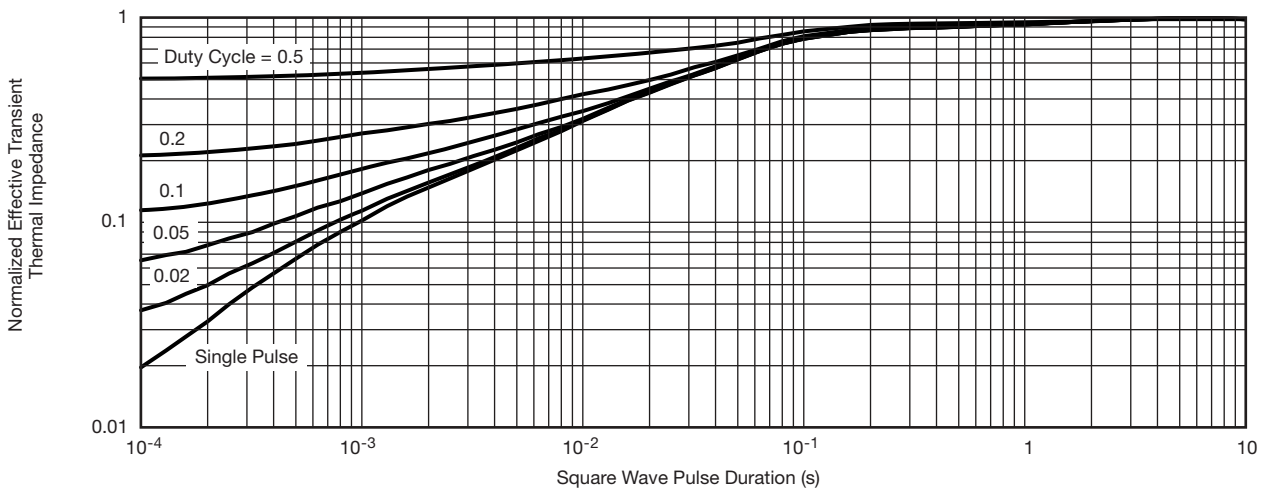
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**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)**Source-Drain Diode Forward Voltage****On-Resistance vs. Gate-to-Source Voltage****Threshold Voltage****Single Pulse Power*** V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified**Safe Operating Area, Junction-to-Ambient**

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-foot thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

Si1414DH

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**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)**Normalized Thermal Transient Impedance, Junction-to-Ambient****Normalized Thermal Transient Impedance, Junction-to-Foot**

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